

# NX3008PBKS

# 30 V, 200 mA dual P-channel Trench MOSFET Rev. 1 — 1 August 2011

Product data sheet

### 1. **Product profile**

## 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

# 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V};$ $T_{amb} = 25 \text{ °C}$	[1]	-	-	-200	mA
Static characte	eristics (per transistor)						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V};$ $I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$		-	2.8	4.1	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	D. D. D.	D4 D0
2	G1	gate TR1	<u>[6                                    </u>	D1 D2
3	D2	drain TR2		
4	S2	source TR2	0	G1 $G2$
5	G2	gate TR2	□1 □2 □3	
6	D1	drain TR1	SOT363 (SC-88)	17
				S1 S2 017aaa260

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX3008PBKS	SC-88	plastic surface-mounted package; 6 leads	SOT363

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
NX3008PBKS	LC%

<sup>[1]</sup> % = placeholder for manufacturing site code.

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	r					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
$V_{GS}$	gate-source voltage			-8	8	V
$I_D$	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	<u>[1]</u>	-	-200	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	-125	mA
I <sub>DM</sub>	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \le 10 \mu s$		-	-0.8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW
				-	320	mW
		T <sub>sp</sub> = 25 °C		-	990	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	445	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-200	mA
ESD maximu	ım rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

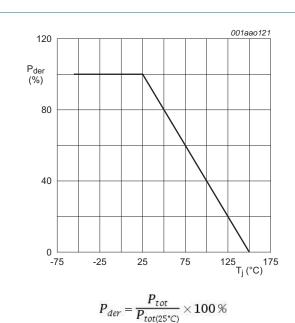
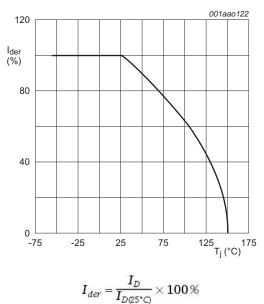
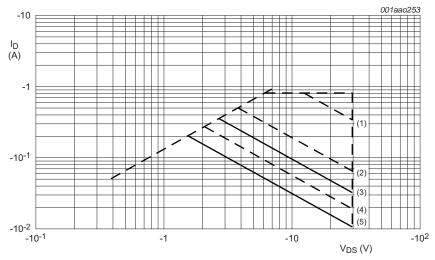


Fig 1. Normalized total power dissipation as a function of junction temperature



 $I_{D(25^{\circ}C)}$ 





I<sub>DM</sub> is a single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (4)  $t_p = 100 \text{ ms}$
- (5) DC;  $T_{amb} = 25 \text{ °C}$ ; 1 cm<sup>2</sup> drain mounting pad

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W
Per transistor	r					
R <sub>th(j-a)</sub>	thermal resistance from junction to	in free air	<u>[1]</u> -	390	445	K/W
	ambient		[2] _	340	390	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

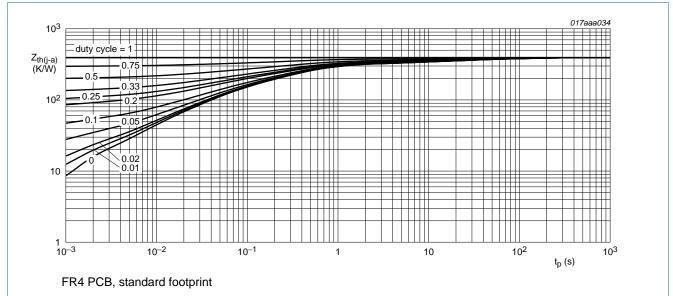


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

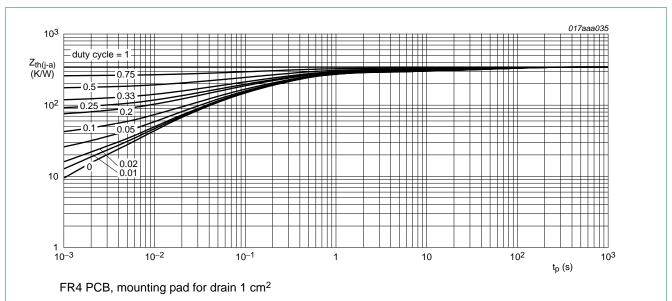


Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.6	-0.9	-1.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.2	-1	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.2	-1	μΑ
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-	nΑ
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-	nΑ
		$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-1	-	nΑ
		$V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-1	-	nΑ
R <sub>DSon</sub> drain-source on resistance	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -200 mA; $T_j$ = 25 °C	-	2.8	4.1	Ω
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -200 mA; $T_j$ = 150 °C	-	5.3	7.8	Ω
		$V_{GS} = -2.5 \text{ V}; I_D = -10 \text{ mA}; T_j = 25 \text{ °C}$	-	5.3	6.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$	-	160	-	mS
Dynamic o	characteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -15 \text{ V}; I_D = -200 \text{ mA};$	-	0.55	0.72	nC
$Q_{GS}$	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.23	-	nC
$Q_GD$	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	31	46	pF
C <sub>oss</sub>	output capacitance	$T_j = 25  ^{\circ}\text{C}$	-	6.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -20 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = -4.5 V;	-	19	38	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	65	130	ns
t <sub>f</sub>	fall time		-	38	-	ns
Source-dr	ain diode (per transistor)					
$V_{SD}$	source-drain voltage	$I_S = -200 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-0.47	-0.88	-1.2	V

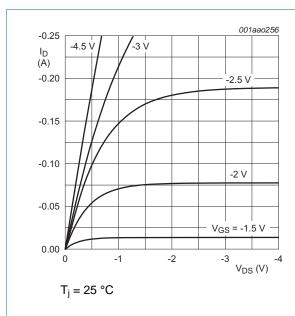
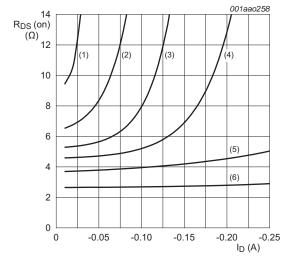


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T<sub>j</sub> = 25 °C

(1)  $V_{GS} = -1.75 \text{ V}$ 

(2)  $V_{GS} = -2.0 \text{ V}$ 

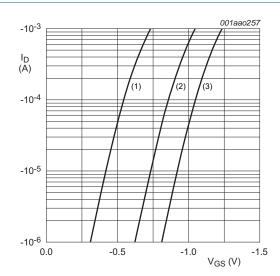
(3)  $V_{GS} = -2.25 \text{ V}$ 

(4)  $V_{GS} = -2.5 \text{ V}$ 

(5)  $V_{GS} = -3.0 \text{ V}$ 

(6)  $V_{GS} = -4.5 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



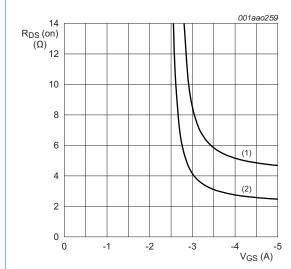
 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

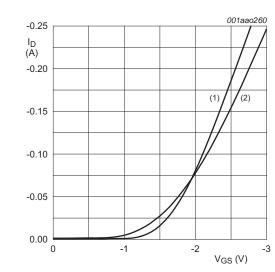


 $I_D = -200 \text{ mA}$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

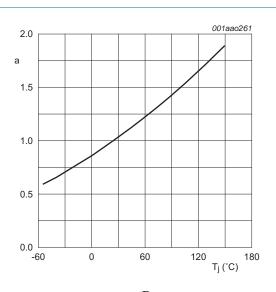


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

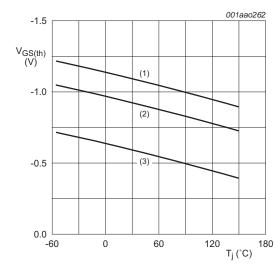
(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

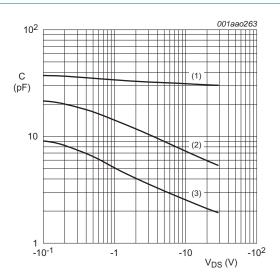
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1)C<sub>iss</sub>
- (2)C<sub>oss</sub>
- (3)C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

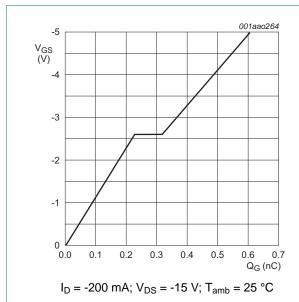


Fig 14. Gate-source voltage as a function of gate charge; typical values

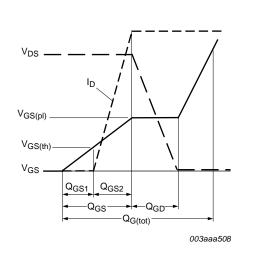
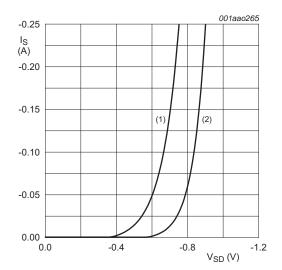


Fig 15. Gate charge waveform definitions

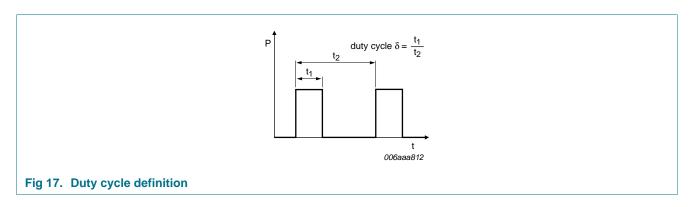


$$V_{GS} = 0 V$$

(2) 
$$T_j = 25 \, ^{\circ}C$$

Fig 16. Source current as a function of source-drain voltage; typical values

# 8. Test information



# 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

**SOT363** 

# 9. Package outline

Plastic surface-mounted package; 6 leads

# 

### **DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

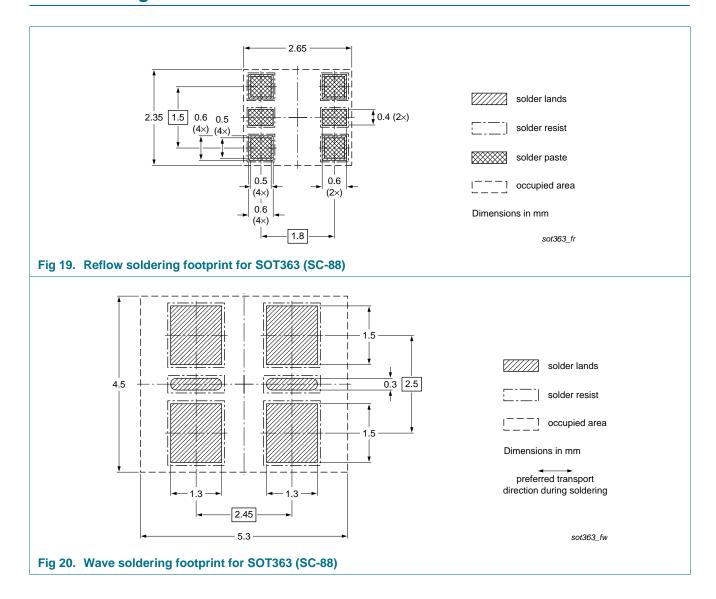
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT363			SC-88		<del>04-11-08</del> 06-03-16

Fig 18. Package outline SOT363 (SC-88)

NX3008PBKS

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# 10. Soldering



Nexperia NX3008PBKS

30 V, 200 mA dual P-channel Trench MOSFET

# 11. Revision history

# Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3008PBKS v.1	20110801	Product data sheet	-	-

# 12. Legal information

### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Nexperia NX3008PBKS

### 30 V, 200 mA dual P-channel Trench MOSFET

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# **Nexperia**

# NX3008PBKS

30 V, 200 mA dual P-channel Trench MOSFET

# 14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Marking
5	Limiting values
6	Thermal characteristics
7	Characteristics
8	Test information1
8.1	Quality information
9	Package outline
10	Soldering13
11	Revision history14
12	Legal information15
12.1	Data sheet status
12.2	Definitions15
12.3	Disclaimers
12.4	Trademarks16
13	Contact information16